

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF THE CLAIMS:**

Claim 1 (Previously Presented) A hybrid substrate comprising:

a first semiconductor layer having a first crystallographic orientation; and

a second semiconductor layer having a second crystallographic orientation which is different from the first crystallographic orientation, wherein said first and second semiconductor layers are separated from each other by a conductive interface that has an upper surface that is in contact with said second semiconductor layer and a lower surface that is in contact with said first semiconductor layer, said conductive interface comprises a hydrophilic surface or a hydrophobic surface of at least one of said semiconductor layers.

Claims 2-3 (Cancelled)

Claim 4 (Original) The hybrid substrate of Claim 1 wherein said first semiconductor layer and the second semiconductor layer are composed of the same or different semiconductor material selected from the group consisting of Si, SiC, SiGe, SiGeC, Ge, GaAs, InAs, InP, other III/V or II/VI compound semiconductors and any combination thereof.

Claim 5 (Original) The hybrid substrate of Claim 1 wherein said first semiconductor layer and the second semiconductor layer are both composed of Si.

Claim 6 (Original) The hybrid substrate of Claim 1 wherein said first semiconductor layer has a (100) crystal orientation and said second semiconductor layer has a (110) crystal orientation.

Claim 7 (Original) The hybrid substrate of Claim 1 wherein said first semiconductor layer has a (110) crystal orientation and said second semiconductor layer has a (100) crystal orientation.

Claim 8 (Original) The hybrid substrate of Claim 1 wherein said first semiconductor layer comprises a relaxed semiconductor material or a stack of a relaxed semiconductor material and a strained semiconductor material.

Claim 9 (Original) The hybrid substrate of Claim 1 wherein said second semiconductor material comprises a relaxed semiconductor material or a stack of a relaxed semiconductor material and a strained semiconductor material.

Claims 10-23 (Cancelled)

Claim 24 (Currently Amended) An integrated semiconductor structure comprising:  
a hybrid structure comprising a first device region having a first crystallographic orientation and a second device region having a second crystallographic orientation, said first crystallographic orientation is different from said second crystallographic orientation, and wherein said hybrid structure comprises a hybrid substrate that comprises a first semiconductor layer having said first crystallographic orientation and a second semiconductor layer having said second crystallographic orientation, said first and second semiconductor layers are separated from each other by a conductive interface;

an isolation region separating said first device region from said second device region; and  
at least one first semiconductor device located in said first device region and at least one second semiconductor device located in said second device region, wherein said first semiconductor device and said second semiconductor device are both bulk-like devices and both devices contain a well region that serves as a body contact.

Claim 25 (Original) The integrated semiconductor structure of Claim 24 wherein the first crystallographic orientation is (110) and the second crystallographic orientation is (100).

Claim 26 (Original) The integrated semiconductor structure of Claim 25 wherein said at least one first semiconductor device is a pFET and the at least one second semiconductor device is an nFET.

Claim 27 (Original) The integrated semiconductor structure of Claim 24 wherein the first crystallographic orientation is (100) and the second crystallographic orientation is (110).

Claim 28 (Original) The integrated semiconductor structure of Claim 27 wherein said at least one first semiconductor device is an nFET and the at least one second semiconductor device is a pFET.

Claim 29 (Original) The integrated semiconductor structure of Claim 24 wherein the first device region includes a regrown semiconductor material located atop a first semiconductor material, said regrown semiconductor material having the same crystallographic orientation as the first semiconductor material.

Claim 30 (Original) The integrated semiconductor structure of Claim 29 wherein said regrown semiconductor material is recessed and another semiconductor material is formed atop the recessed regrown semiconductor material.

Claim 31 (Original) The integrated semiconductor structure of Claim 30 wherein said another semiconductor material is a strained semiconductor or a stack comprising a relaxed semiconductor and a strained semiconductor.

Claim 32 (Original) The integrated semiconductor structure of Claim 29 wherein said regrown semiconductor material is a semiconductor selected from the group consisting of Si, SiC, SiGe, SiGeC, Ge, GaAs, InAs, InP, other III/V or II/VI compound semiconductors and any combination thereof.

Claim 33 (Original) The integrated semiconductor structure of Claim 24 wherein said first and second semiconductor device regions both include strained Si.

Claim 34 (Original) The integrated semiconductor structure of Claim 29 wherein said regrown semiconductor material comprises a strained semiconductor layer located atop a relaxed semiconductor layer.

Claims 35-58 (Cancelled)